IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

Patent Application

Inventors: Julia Wan-Ping Hsu et al   **Case No.:** 4 – 5

Serial No.: Unknown   **Group Art Unit:** Unknown

Filing Date: Dec. 12, 2003   **Examiner:** Unknown

Title: IMPROVED LAYERS OF GROUP III-NITRIDE SEMICONDUCTOR

Mail Stop: Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

STATEMENT AND REQUEST UNDER 37 C.F.R. 1.63(d)

The above-referenced patent application is a continuation under 37 CFR 1.53(b) of parent Patent Application No. 10/179,806, which was filed on June 25, 2002.

This application is being filed in the names of fewer than all the inventors of the parent patent application. Furthermore, this application contains no matter that would have been new matter in the parent patent application.

With this continuation application, a copy of the declaration under 37 CFR § 1.63 for the parent application is being filed.
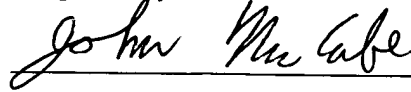
Applicants request deletion of the name of Mr. Nils G. Weimann as an inventor in this continuation application, because Mr. Weimann is not an inventor for claims 1 – 13 being pursued herein.

        NO FEE.

In the event of any non-payment or improper payment of a required fee, the Commissioner is authorized to charge or to credit Lucent Technologies Deposit Account No. 12-2325 to correct the error.

Respectfully,

John F. McCabe, Reg. No. 42,854
Telephone: 908-582-6866

Date: Dec. 12, 2003
Lucent Technologies Inc.
Docket Administrator
101 Crawfords Corner Road (Rm. 3J-219)
Holmdel, New Jersey 07733

INFORMATION DISCLOSURE STATEMENT	Case Name.	J.W. Hsu 4-5
	Serial No.	J.W. Hsu, et al.
	Applicant:	
	Filing Date:	December 12, 2003
	Group:	

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Dat
	AA	6,086,673	July 11, 2000	Richard J. Molnar	117	90	April 2, 1998
	AB	2002/0086534	7/4/02	Cuomo et al.	438	689	11/30/01

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation

OTHER (including Author, Title, Date, Pertinent Pages, etc.)

	AC	E.J. Miller et al., "Reduction of reverse-bias leakage current in Schottky diodes on GaN grown by molecular-beam epitaxy using surface modification with an atomic force microscope", Journal of Applied Physics, Vol. 91, No. 12, June 15, 2002, pages 9821-9826.
	AD	E.J. Miller et al., "Reverse-bias leakage current reduction in GaN Schottky diodes by surface modification with an atomic force microscope," Abstract from Technical Program Session V of Electronic Materials Conference, Santa Barbara, CA (June 25-27, 2002) 1 page (Note: may have been published before June 25, 2002).
	AE	E.J. Miller et al., "CHARACTERIZATION AND LOCAL PASSIVATION OF REVERSE-BIAS CURRENT LEAKAGE PATHS IN AN AlGaN/GaN HETEROSTRUCTURE, Abstract from Nov. 2001 MRS Fall Meeting," Symposium 1, Session I 10.7 (1 page), publ.'d online at www. mrs.org/meetings/fall 2001.
	AF	Lee, J.J., et al., "MBE Growth of Wurtzite GaN on LaAlO₃ (100) Substrate," Journal of Crystal Growth, Vol. 213, No. 1-2, pp. 33-39, May 2000.

***References listed beyond AZ would list as AA-1, AB-2, AC-3 thru AZ-26.
***Note First Page ONLY Header/Footer. Subsequent pages must ONLY have <u>page # layout</u> as header

EXAMINER	DATE CONSIDERED

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

PT968-1.97Form